

## **Notification about the transfer of the semiconductor business**

The semiconductor business of Panasonic Corporation was transferred on September 1, 2020 to Nuvoton Technology Corporation (hereinafter referred to as "Nuvoton"). Accordingly, Panasonic Semiconductor Solutions Co., Ltd. became under the umbrella of the Nuvoton Group, with the new name of Nuvoton Technology Corporation Japan (hereinafter referred to as "NTCJ").

In accordance with this transfer, semiconductor products will be handled as NTCJ-made products after September 1, 2020. However, such products will be continuously sold through Panasonic Corporation.

Publisher of this Document is NTCJ.

If you would find description "Panasonic" or "Panasonic semiconductor solutions", please replace it with NTCJ.

※ Except below description page

"Request for your special attention and precautions in using the technical information and semiconductors described in this book"

**Nuvoton Technology Corporation Japan**



# FC6B22160L

## Gate resistor installed Dual N-channel MOS FET

For lithium-ion secondary battery protection circuits

### ■ Features

- Low source-source ON resistance:  $R_{ss(on)}$  typ. = 4.7 m $\Omega$  (VGS = 4.5 V)
- CSP (Chip Size Package)
- RoHS compliant (EU RoHS / MSL: Level 1 compliant)

### ■ Marking Symbol: 36

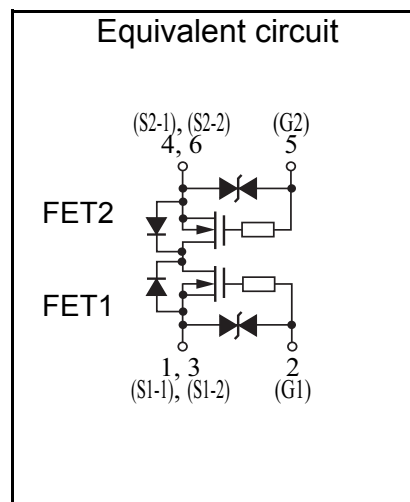
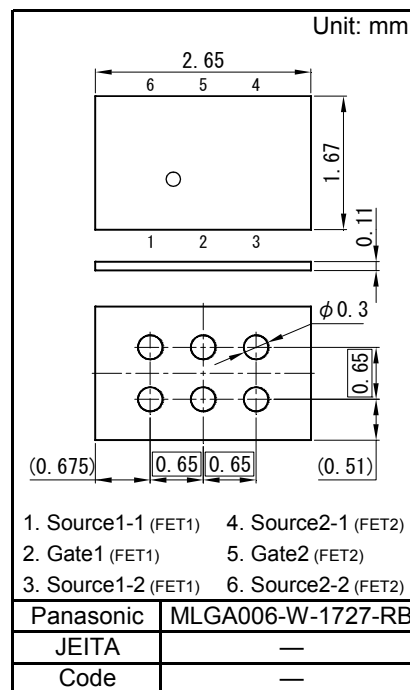
### ■ Packaging

Embossed type (Thermo-compression sealing) : 10 000 pcs / reel (standard)

### ■ Absolute Maximum Ratings Ta = 25 °C

| Parameter                 | Symbol              | Rating      | Unit     |
|---------------------------|---------------------|-------------|----------|
| Source-source Voltage     | VSS                 | 20          | V        |
| Gate-source Voltage       | VGS                 | ±8          | V        |
| Source Current            | DC <sup>*1</sup>    | IS1         | 8 A      |
|                           | DC <sup>*2</sup>    | IS2         | 17 A     |
|                           | Pulse <sup>*3</sup> | ISp         | 80 A     |
| Total Power Dissipation   | DC <sup>*1</sup>    | PD1         | 0.45 W   |
|                           | DC <sup>*2</sup>    | PD2         | 2.1 W    |
| Channel Temperature       | Tch                 | 150         | °C       |
| Storage Temperature Range | Tstg                | -55 to +150 | °C       |
| Thermal Resistance (ch-a) | DC <sup>*1</sup>    | Rth1        | 278 °C/W |
|                           | DC <sup>*2</sup>    | Rth2        | 59 °C/W  |

- Note \*1 Mounted on FR4 board ( 25.4 mm × 25.4 mm × t1.0 mm )  
 using the minimum recommended pad size (36 $\mu$ m Copper ).  
 \*2 Mounted on Ceramic substrate (70 mm × 70 mm × t1.0 mm).  
 \*3 t = 10  $\mu$ s, Duty Cycle ≤ 1 %



■ Electrical Characteristics Ta = 25 °C ± 3 °C

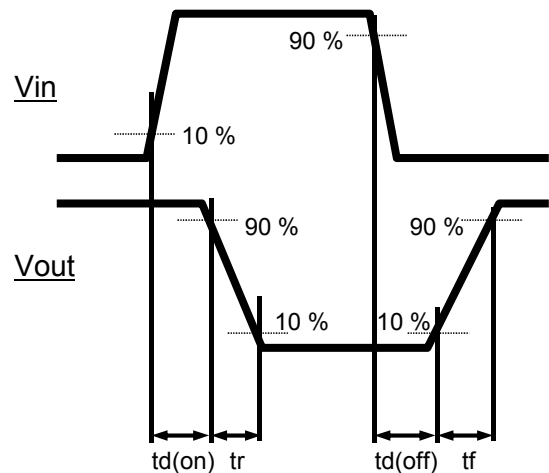
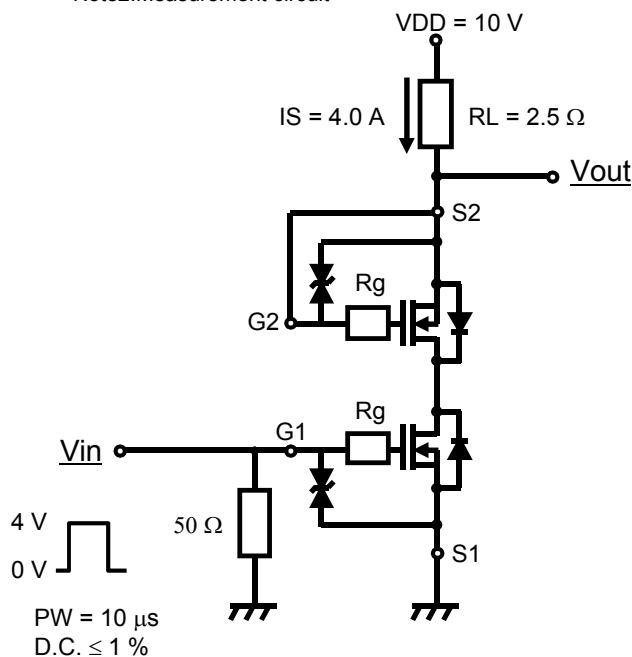
| Parameter                         | Symbol   | Conditions                       | Min  | Typ  | Max  | Unit |
|-----------------------------------|----------|----------------------------------|------|------|------|------|
| Source-source Breakdown Voltage   | VSSS     | IS = 1 mA, VGS = 0 V             | 20   |      |      | V    |
| Zero Gate Voltage Source Current  | ISSS     | VSS = 20 V, VGS = 0 V            |      |      | 1.0  | μA   |
| Gate-source Leakage Current       | IGSS     | VGS = ±8 V, VSS = 0 V            |      |      | ±10  | μA   |
|                                   |          | VGS = ±5 V, VSS = 0 V            |      |      | ±1.0 |      |
| Gate-source Threshold Voltage     | Vth      | IS = 1.1 mA, VSS = 10 V          | 0.35 | 0.90 | 1.4  | V    |
| Source-source On-state Resistance | RSS(on)1 | IS = 4.0 A, VGS = 4.5 V          | 3.5  | 4.7  | 6.2  | mΩ   |
|                                   | RSS(on)2 | IS = 4.0 A, VGS = 4.0 V          | 3.6  | 4.8  | 6.4  |      |
|                                   | RSS(on)3 | IS = 4.0 A, VGS = 3.8 V          | 3.7  | 4.9  | 6.6  |      |
|                                   | RSS(on)4 | IS = 4.0 A, VGS = 3.1 V          | 3.9  | 5.2  | 8.6  |      |
|                                   | RSS(on)5 | IS = 4.0 A, VGS = 2.5 V          | 4    | 6    | 11.8 |      |
| Body Diode Forward Voltage        | VF(s-s)  | IF = 4.0 A, VGS = 0 V            |      | 0.8  | 1.2  | V    |
| Input Capacitance *1              | Ciss     | VSS = 10 V, VGS = 0 V, f = 1 MHz |      | 3250 |      | pF   |
| Output Capacitance *1             | Coss     |                                  |      | 290  |      |      |
| Reverse Transfer Capacitance *1   | Crss     |                                  |      | 250  |      |      |
| Turn-on delay Time *1,*2          | td(on)   | VDD = 10 V, VGS = 0 to 4.0 V     |      | 1.2  |      | μs   |
| Rise Time *1,*2                   | tr       | IS = 4.0 A                       |      | 2.4  |      |      |
| Turn-off delay Time *1,*2         | td(off)  | VDD = 10 V, VGS = 4.0 to 0 V     |      | 8.1  |      | μs   |
| Fall Time *1,*2                   | tf       | IS = 4.0 A                       |      | 3.9  |      |      |
| Total Gate Charge *1              | Qg       | VDD = 10 V                       |      | 35   |      | nC   |
| Gate-source Charge *1             | Qgs      | VGS = 0 to 4.0 V,                |      | 5    |      |      |
| Gate-drain Charge *1              | Qgd      | IS = 4.0 A                       |      | 10   |      |      |

Note Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 Measuring methods for transistors.

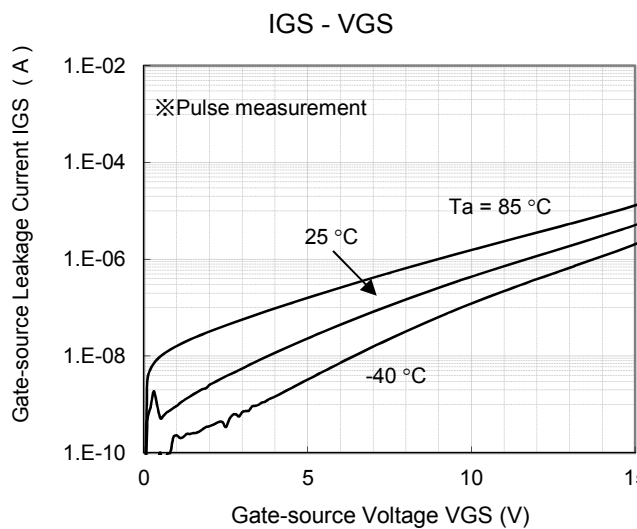
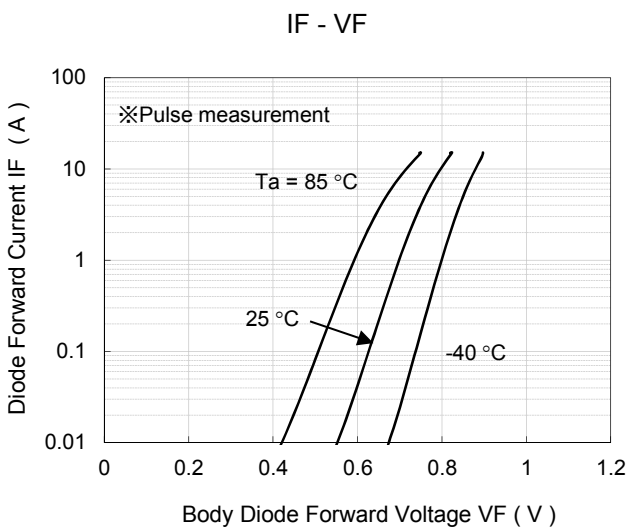
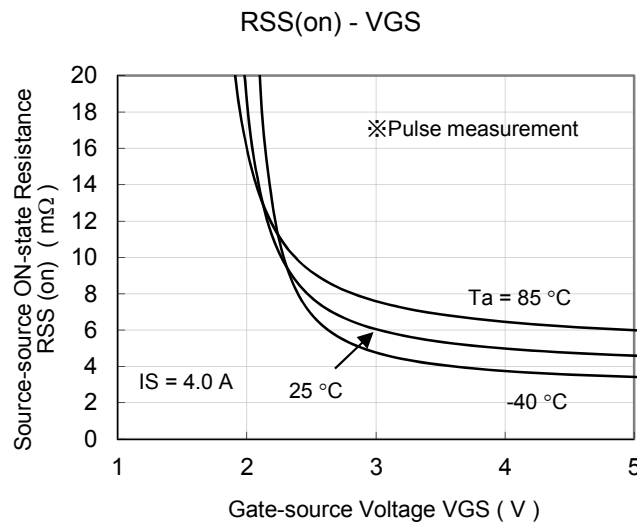
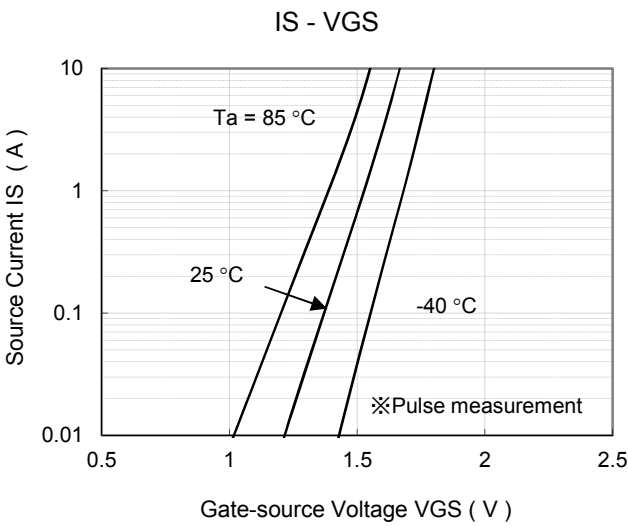
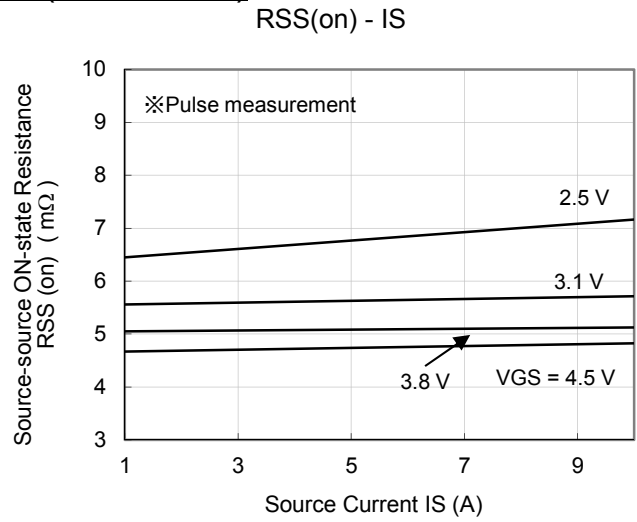
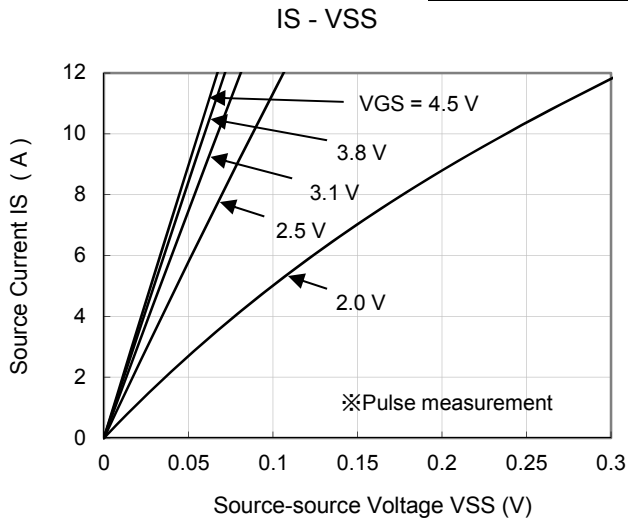
\*1 Guaranteed by design, not subject to production testing

\*2 Measurement circuit for Turn-on Delay Time / Rise Time / Turn-off Delay Time / Fall Time

Note2: Measurement circuit

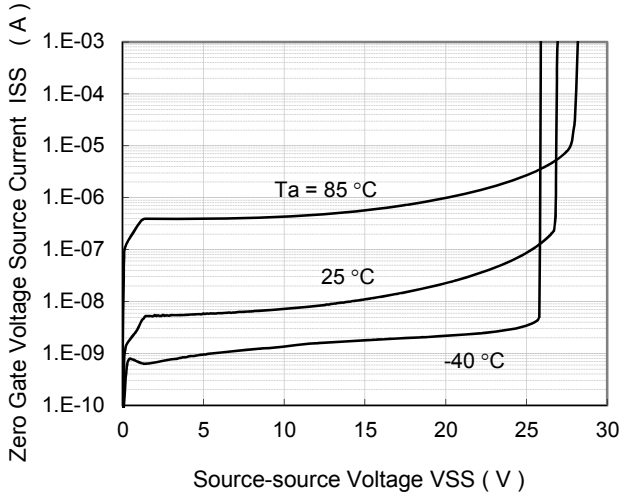


Technical Data ( reference )

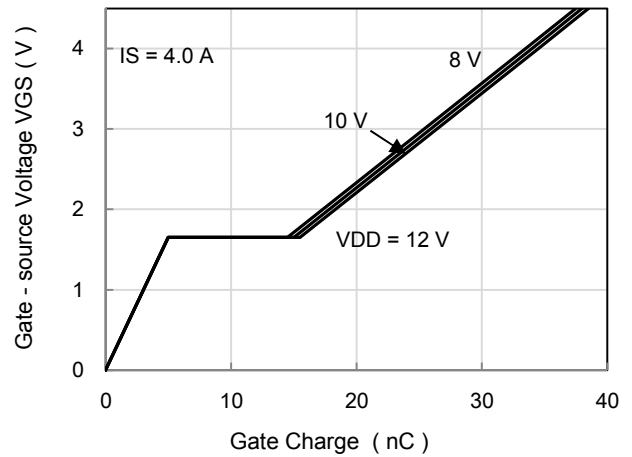


Technical Data ( reference )

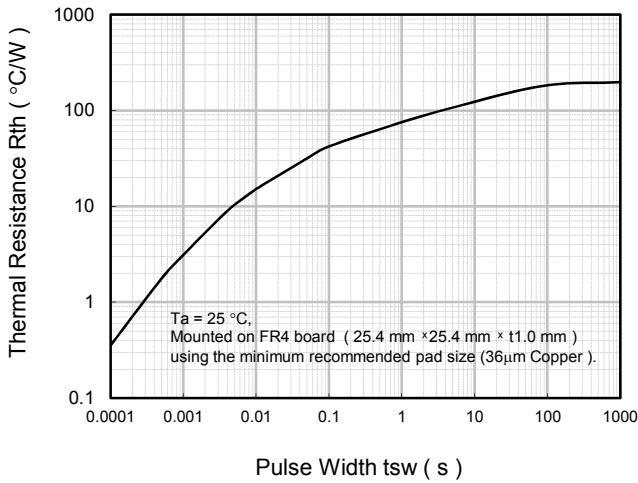
ISS - VSS



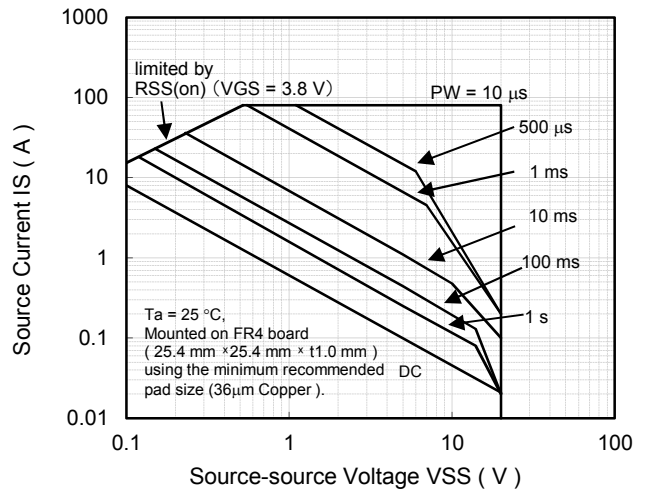
Dynamic Input/Output Characteristics



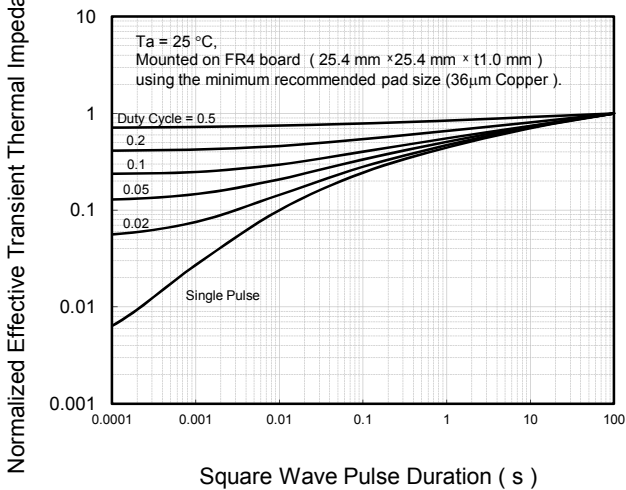
$R_{th} - t_{sw}$



Safe Operating Area

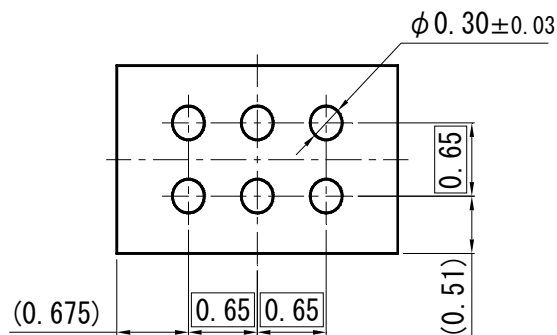
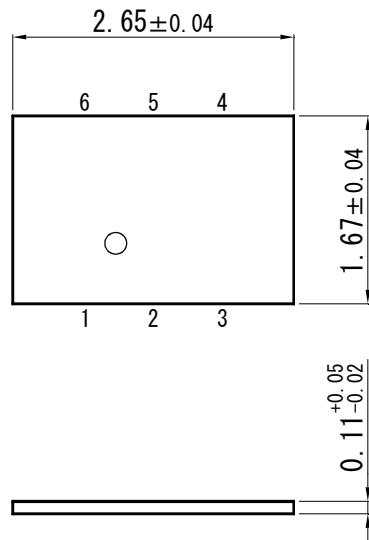


Thermal Response

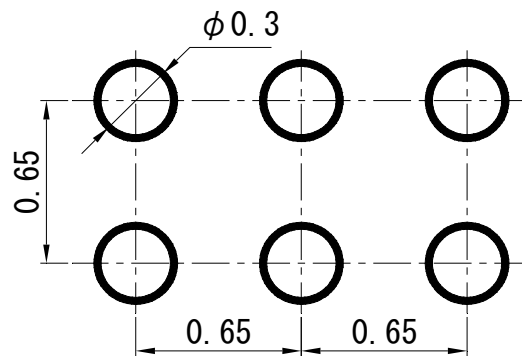


MLGA006-W-1727-RB

Unit: mm



■ Land Pattern (Reference) (Unit: mm)



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